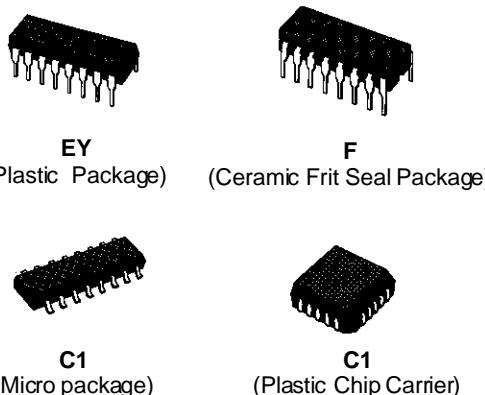


QUAD LOW-TO-HIGH VOLTAGE LEVEL SHIFTER

- INDEPENDENCE OF POWER SUPPLY SEQUENCE CONSIDERATIONS – V_{CC} CAN EXCEED V_{DD} , INPUT SIGNALS CAN EXCEED BOTH V_{CC} AND V_{DD}
- UP AND DOWN LEVEL-SHIFTING CAPABILITY
- THREE-STATE OUTPUTS WITH SEPARATE ENABLE CONTROLS
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED AT 20V FOR HCC DEVICE
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

controls produces a high-impedance state in the corresponding output.



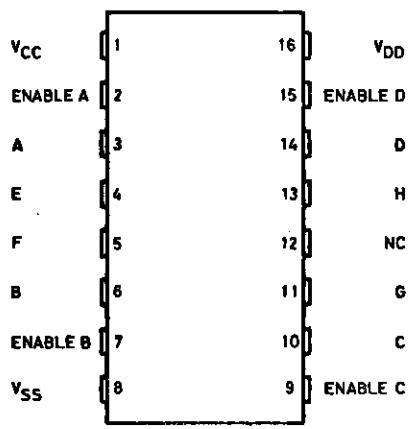
ORDER CODES :

HCC40109BF HCF40109BM1
 HCF40109BEY HCF40109BC1

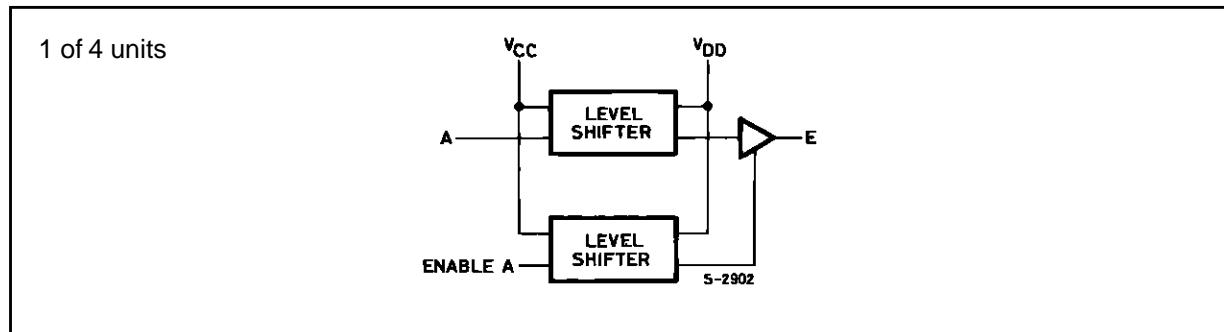
DESCRIPTION

The **HCC40109B** (extended temperature range) and **HCF40109B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage. The **HCC/HCF40109B** contains four low-to-high-voltage level-shifting circuits. Each circuit will shift a low-voltage digital-logic input signal (A, B, C, D) with logical 1 = V_{CC} and logical 0 = V_{SS} to a higher-voltage output signal (E, F, G, H) with logical 1 = V_{DD} and logical 0 = V_{SS} . The **HCC/HCF40109B**, unlike other low-to-high level-shifting circuits, does not require the presence of the high-voltage supply (V_{DD}) before the application of either the low-voltage supply (V_{CC}) or the input signals. There are no restrictions on the sequence of application of V_{DD} , V_{CC} , or the input signals. In addition, there are no restrictions on the relative magnitudes of the supply voltages or input signals within the device maximum ratings ; V_{CC} may exceed V_{DD} , and input signals may exceed V_{CC} , and V_{DD} . When operated in the mode $V_{CC} > V_{DD}$, the **HCC/HCF40109B**, will operate as a high-to-low level-shifter. The **HCC/HCF 40109B** also features individual three-state output capability. A low level on any of the separately enabled three-state output

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	– 0.5 to + 20 – 0.5 to + 18	V V
V_i	Input Voltage	– 0.5 to V_{DD} + 0.5	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200 100	mW mW
T_{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	°C °C
T_{stg}	Storage Temperature	– 65 to + 150	°C

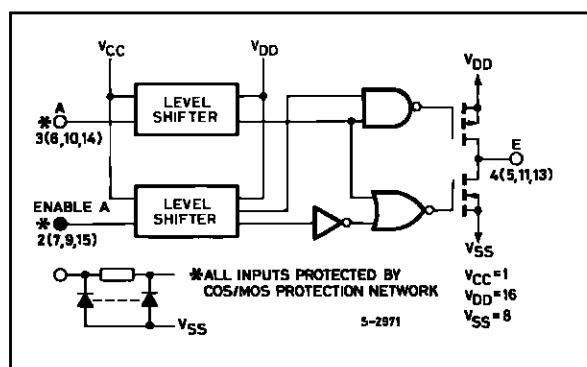
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage are with respect to V_{SS} (GND).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	°C °C

LOGIC DIAGRAM



TRUTH TABLE

Mode	Inputs		Outputs
	A, B, C, D	Enable	
Low to High Level Shift	0	1	0
	1	1	1
	X	0	Z

LOGIC 0 = LOW (V_{SS})

X = Don't Care.

Z = High Impedance.

LOGIC 1 = V_{CC} at INPUTS and V_{DD} at OUTPUTS.

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter	Test Conditions					Value						Unit	
		V_I (V)	V_O (V)	I_{IO} (μ A)	V_{CC} (V)	V_{DD} (V)	T_{Low}^*		25°C			T_{High}^*		
							Min	Max.	Min.	Typ.	Max.	Min.	Max.	
I_L	Quiescent Current	HCC Types	0/ 5			5		1		0.02	1		30	μ A
			0/10			10		2		0.02	2		60	
			0/15			15		4		0.02	4		120	
			0/20			20		20		0.04	20		600	
		HCF Types	0/ 5			5		4		0.02	4		30	
			0/10			10		8		0.02	8		60	
			0/15			15		16		0.02	16		120	
		V_{OH}	0/ 5	< 1		5	4.95		4.95			4.95		V
			0/10	< 1		10	9.95		9.95			9.95		
			0/15	< 1		15	14.95		14.95			14.95		
V_{OL}	Output Low Voltage	HCC Types	5/0	< 1		5		0.05			0.05		0.05	V
			10/0	< 1		10		0.05			0.05		0.05	
			15/0	< 1		15		0.05			0.05		0.05	
V_{IH}	Input High Voltage	HCC Types	1/9	< 1	5	10	3.5		3.5			3.5		V
			1.5/13.5	< 1	10	15	7		7			7		
V_{IL}	Input Low Voltage	HCC Types	1/9	< 1	5	10		1.5			1.5		1.5	V
			1.5/13.5	< 1	10	15		3			3		3	
I_{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	-2		-1.6	-3.2		-1.15		mA
			0/ 5	4.6		5	-0.64		-0.51	-1		-0.36		
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9		
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4		
		HCF Types	0/ 5	2.5		5	-1.53		-1.36	-3.2		-1.1		
			0/ 5	4.6		5	-0.52		-0.44	-1		-0.36		
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9		
			0/15	13.5		15	-3.6		-3.0	-6.8		-2.4		
I_{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36		mA
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
			0/18	Any Input			18	± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A
		HCF Types	0/15				15	± 0.3		$\pm 10^{-5}$	± 0.3		± 1	

* $T_{Low} = -55^\circ\text{C}$ for HCC device : -40°C for HCF device.* $T_{High} = +125^\circ\text{C}$ for HCC device : $+85^\circ\text{C}$ for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with $V_{DD} = 5\text{V}$, 2V min. with $V_{DD} = 10\text{V}$, 2.5V min. with $V_{DD} = 15\text{V}$.

** Forced output disabled

STATIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Conditions					Value						Unit		
		V_I (V)	V_O (V)	$ I_O $ (V)	V_{CC} (V)	V_{DD} (V)	T_{Low}^*		25 °C			T_{High}^*			
							Min.	Max.	Min.	Typ.	Max.	Min.	Max.		
I_{OH} , I_{OL}^{**}	3-State Output Leakage Current	HCC Types	0/18	0/18			18		± 0.4		$\pm 10^{-4}$	± 0.4		± 12	μA
		HCF Types	0/15	0/15			15		± 1.0		$\pm 10^{-4}$	± 1.0		± 7.5	
C_I	Input Capacitance		Any Input							5	7.5			pF	

* $T_{Low} = -55^\circ C$ for HCC device : $-40^\circ C$ for HCF device.

* $T_{High} = +125^\circ C$ for HCC device : $+85^\circ C$ for HCF device.

The Noise Margin for both "1" and "0" level is : 1V min. with $V_{DD} = 5V$, 2V min. with $V_{DD} = 10V$, 2.5V min. with $V_{DD} = 15V$.

** Forced output disabled

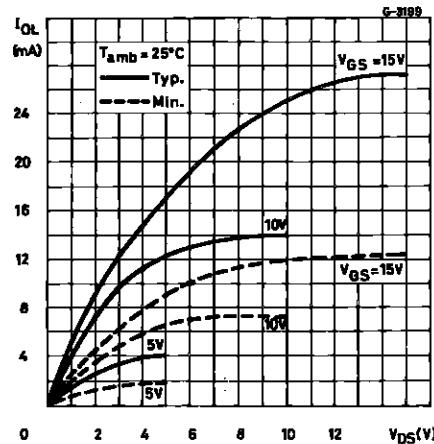
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^\circ C$, $C_L = 50pF$, $R_L = 200k\Omega$,
typical temperature coefficient for all V_{DD} values is $0.3\%/\text{ }^\circ C$, all input rise and fall time = 20ns)

Symbol	Parameter	Shifting Mode	Test Conditions			Value			Unit
			V_{CC} (V)	V_{DD} (V)	Min.	Typ.	Max.		
t_{PHL} , t_{PLH}	Propagation Delay Time (data input to output) High to Low Level	L - H	5	10		300	600		ns
			5	15		220	440		
			10	15		180	360		
		H - L	10	5		850	1600		
			15	5		850	1600		
	Low to High Level	L - H	15	10		290	580		ns
			5	10		130	260		
			5	15		120	240		
		H - L	10	15		70	140		
			10	5		230	460		
t_{PHZ}	3-State Disable Delay Time Output High to High Impedance	L - H	15	5		230	460		ns
			15	10		80	160		
			5	10		60	120		
		H - L	5	15		50	100		
			10	15		35	70		
	High Impedance to Output High	L - H	10	5		120	240		ns
			15	5		120	240		
			15	10		40	80		
		H - L	5	10		320	640		
			5	15		230	460		
t_{PLZ}	Output Low to High Impedance	L - H	10	15		180	360		ns
			10	5		800	1500		
			15	5		800	1500		
		H - L	15	10		280	560		
			5	10		370	740		
		L - H	5	15		300	600		ns
			10	15		250	500		
			10	5		850	1600		
		H - L	15	5		850	1600		
			15	10		350	700		

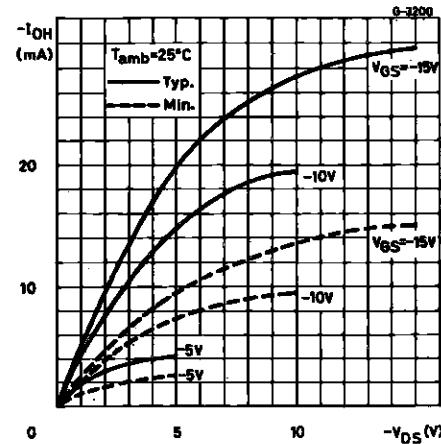
DYNAMIC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Shifting Mode	Test Conditions			Unit	
			V _{CC} (V)	V _{DD} (V)	Min.		
t _{PZL}	High Impedance to Output Low	L - H	5	10		100	200
			5	15		80	160
			10	15		40	80
		H - L	10	5		120	240
			15	5		120	240
			15	10		40	80
			5	10		50	100
t _{THL} , t _{T LH}	Transition Time	L - H	5	15		40	80
			10	15		40	80
			10	5		100	200
		H - L	15	5		100	200
			15	10		50	100

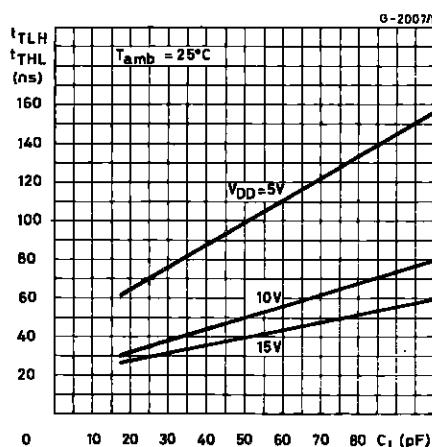
Output Low (sink) Current Characteristics.



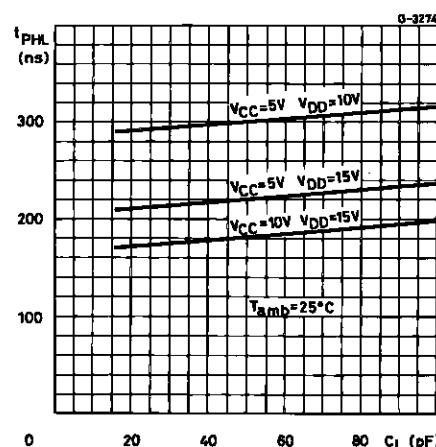
Output High (source) Current Characteristics.



Typical Transition Time vs. Load Capacitance.

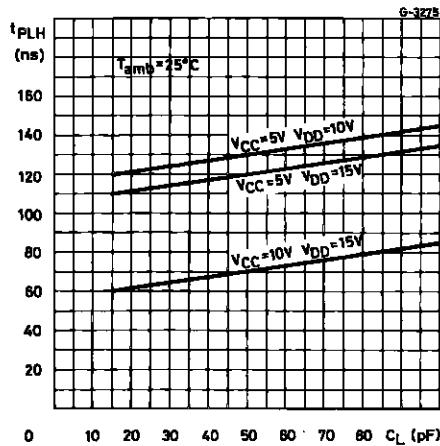


Typical High-to-low Propagation Delay Time vs. Load Capacitance.

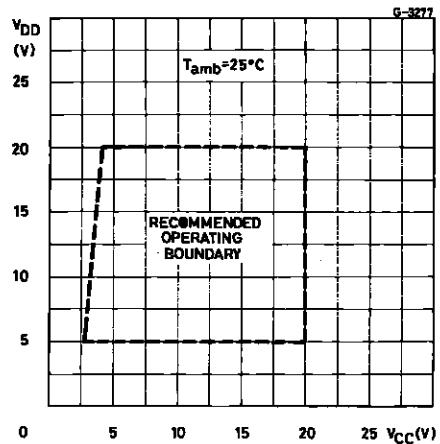


HCC/HCF40109B

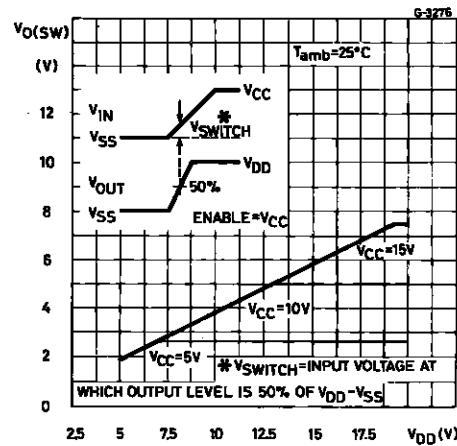
Typical Low-to-high Propagation Delay Time vs. Load Capacitance.



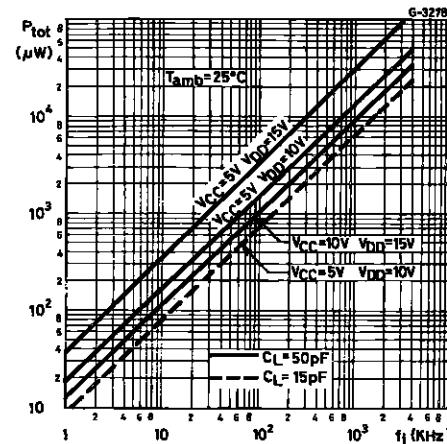
High-level Supply Voltage vs. Low-level Supply Voltage.



Typical Input Switching vs. High-level Supply Voltage.

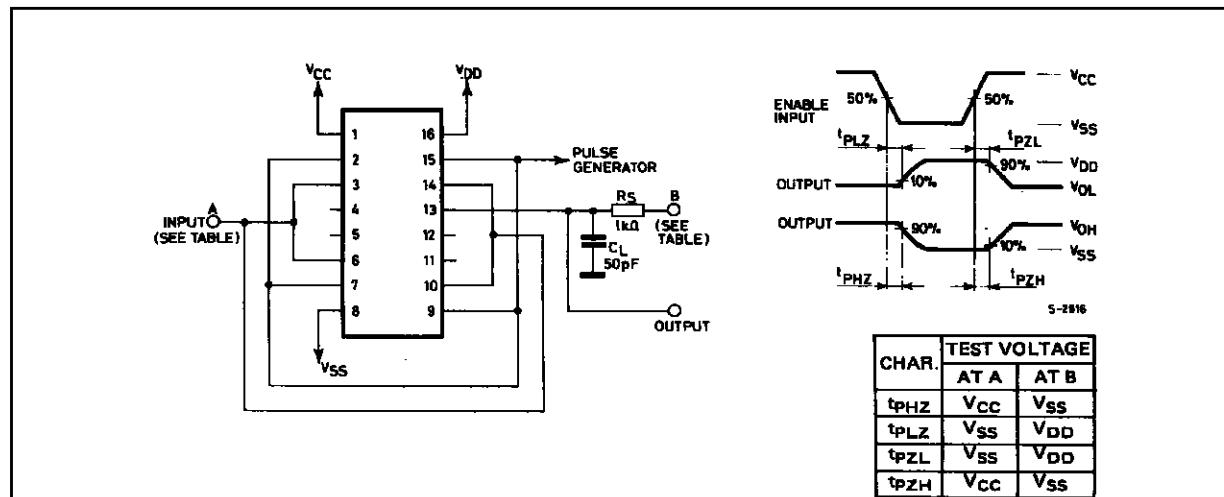


Typical Dynamic Power Dissipation vs. Input Frequency.



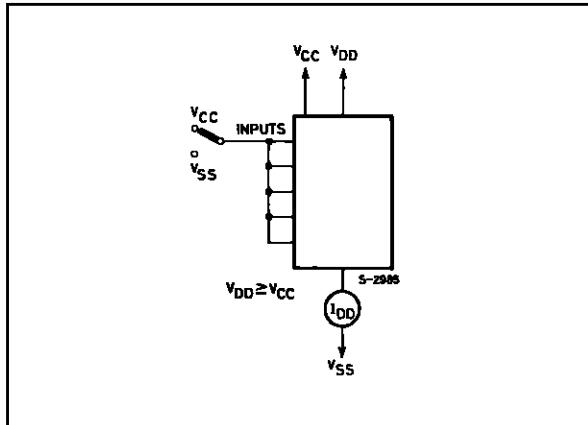
TEST CIRCUITS

Output Enable Delay Times Test Circuit and Waveforms.

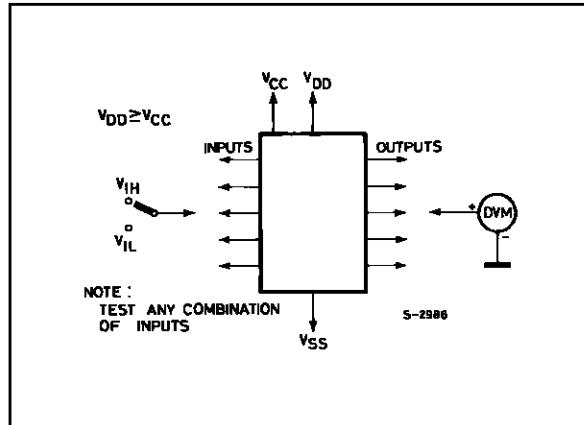


TEST CIRCUITS (continued)

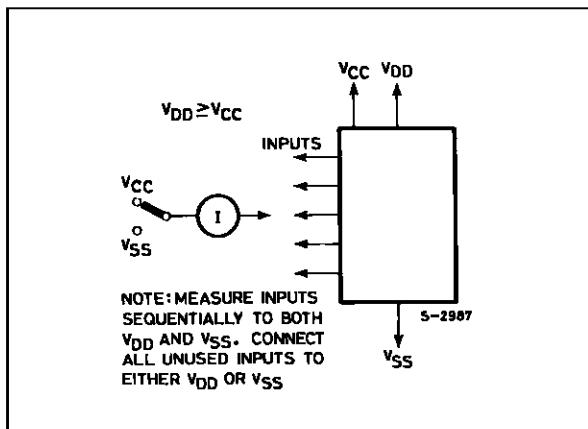
Quiescent Device Current.



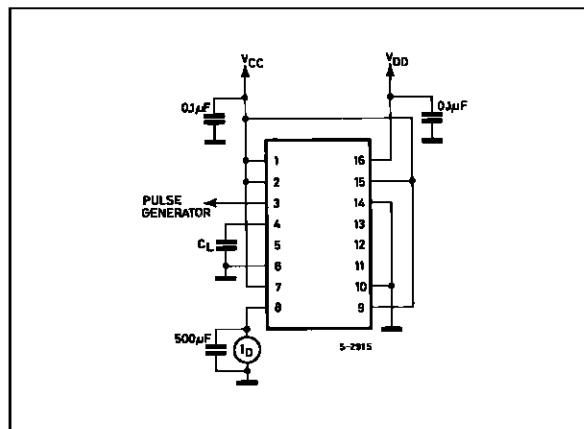
Input Voltage.



Input Leakage Current.

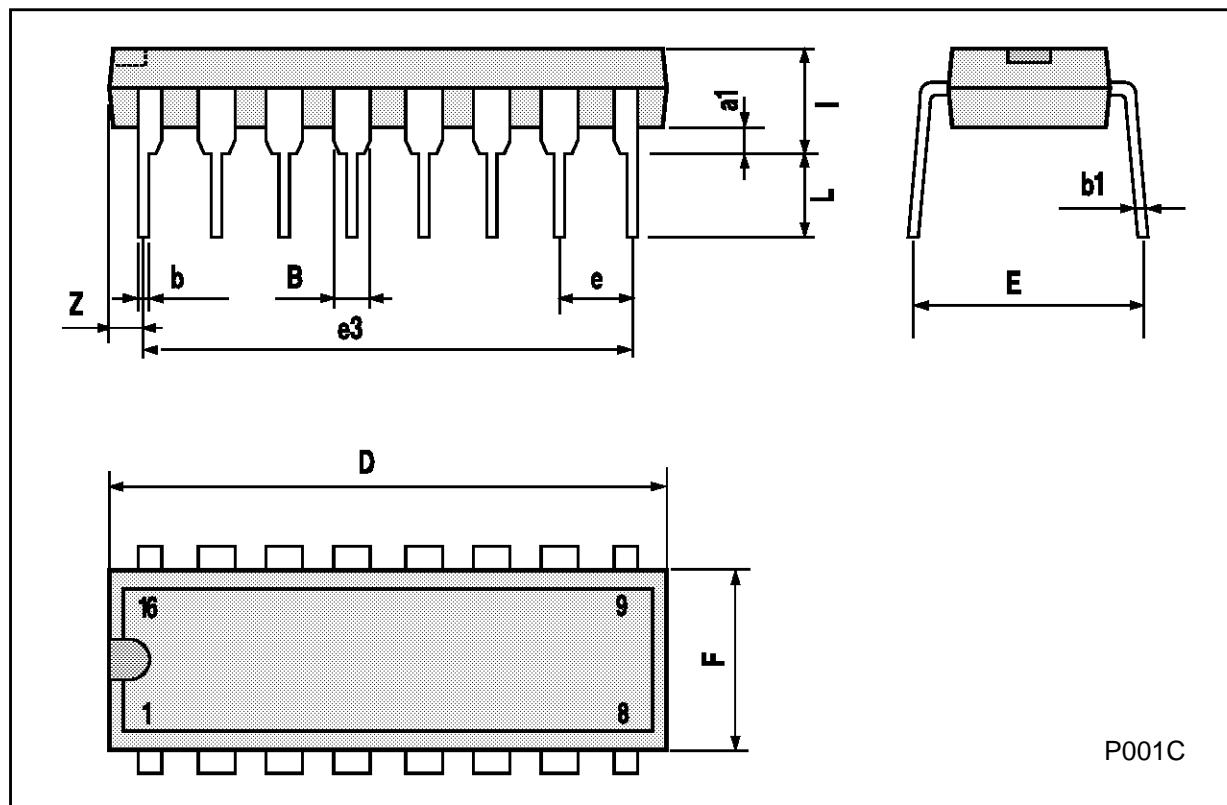


Dynamic Power Dissipation.



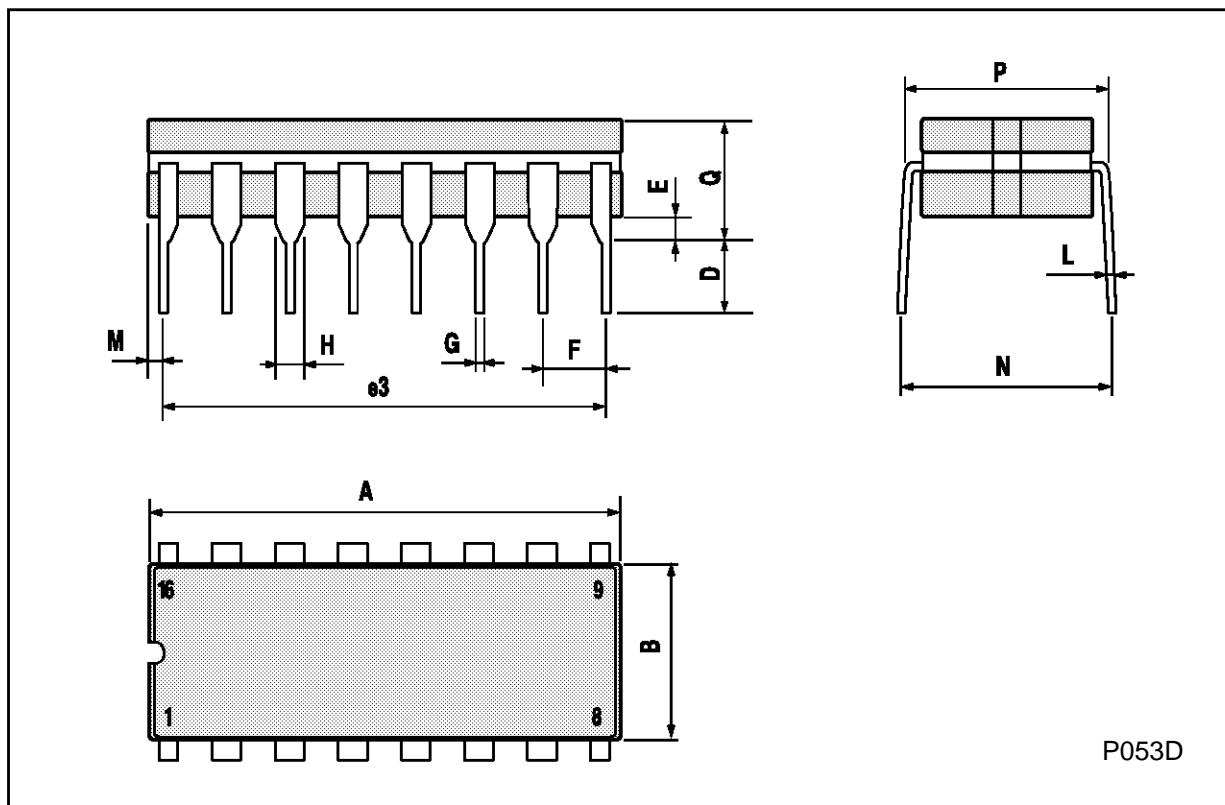
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



Ceramic DIP16/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



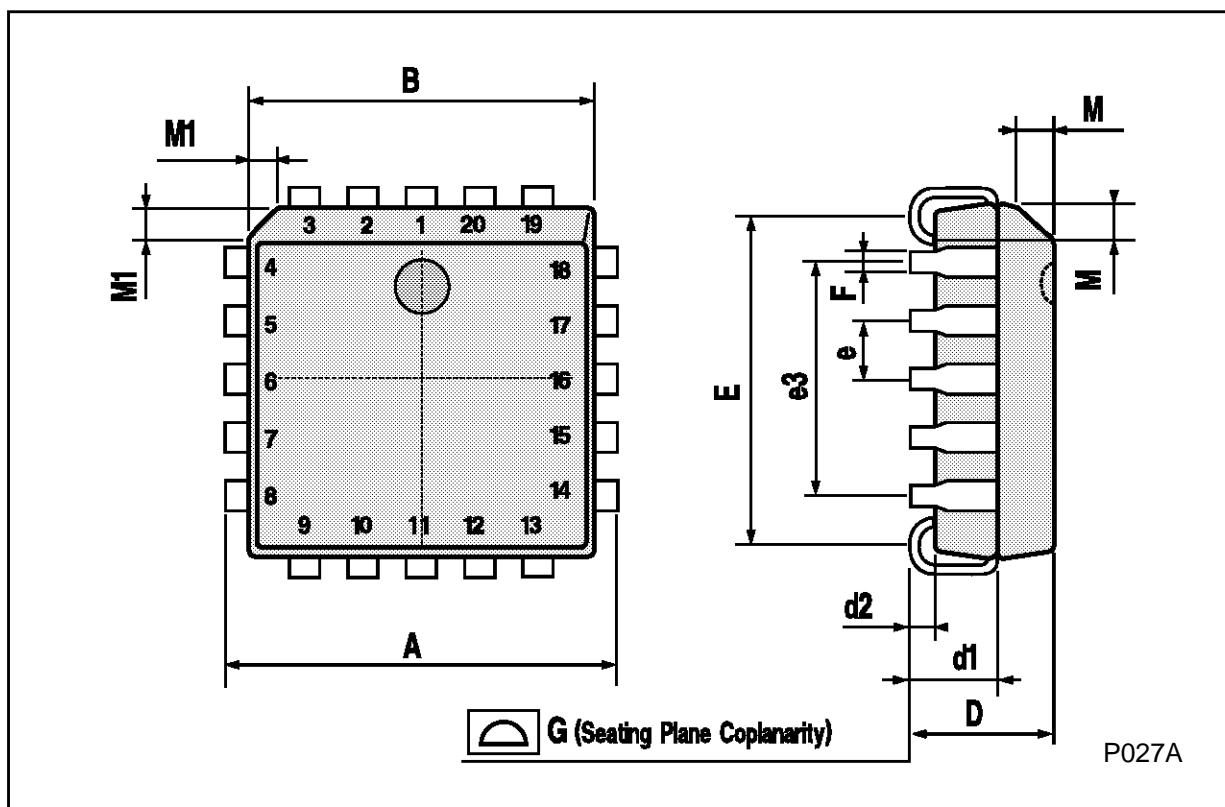
SO16 (Narrow) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1			45° (typ.)			
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S			8° (max.)			



PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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